

ABSTRACT

An exemplary embodiment of the present invention integrates an absorbing layer into the emitting mirror of a 5 VCSEL to reduce the reflectivity of the emitting mirror as seen by the feedback optical wave. The absorbing layer may be made of a suitable semiconductor material, such as a GaAs layer in a laser emitting near 850 nm or highly doped p-layer, and may disposed epitaxially in a semiconductor or 10 metamorphic mirror. Alternatively, a metal layer may be disposed in the dielectric portion of a hybrid mirror or all-dielectric mirror.

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